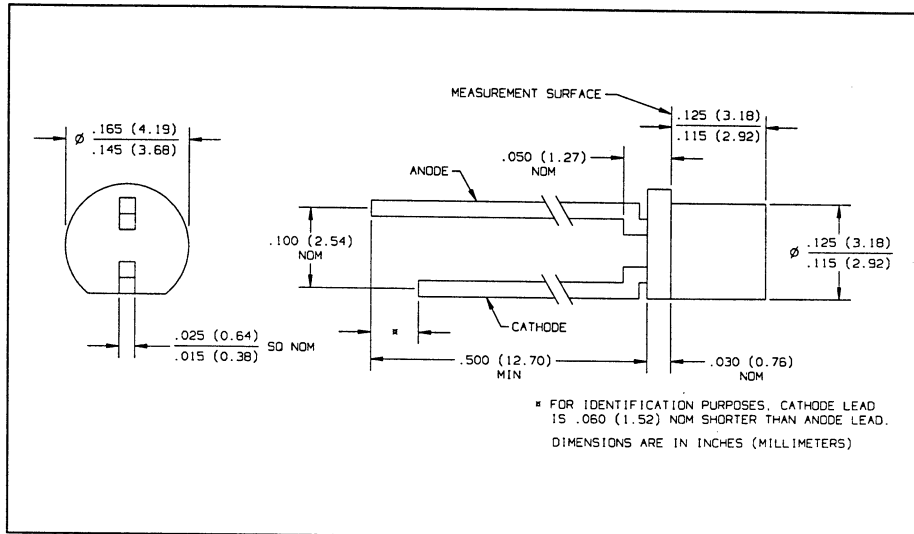
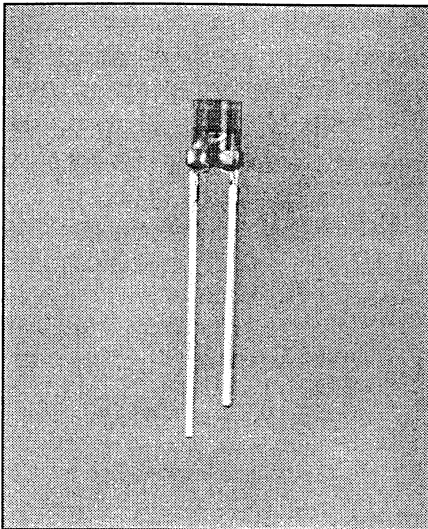


GaAlAs Plastic Infrared Emitting Diode Type OP266W



Features

- Wide irradiance pattern
- Mechanically and spectrally matched to the OP506W
- Small package size for space limited applications
- T-1 package style
- Significantly higher power output than GaAs at equivalent drive currents

Description

The OP266W is an 890 nm high intensity gallium aluminum arsenide infrared emitting diode molded in an IR transmissive amber-tinted epoxy package. This package is a T-1 style in all respects except for the length of the plastic package. Lead spacing on this part is .100 inch (2.54 mm).

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

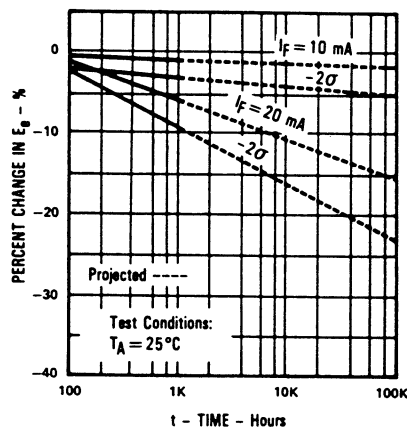
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Storage and Operating Temperature Range	-40°C to $+100^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 Sec. with soldering iron]	260°C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

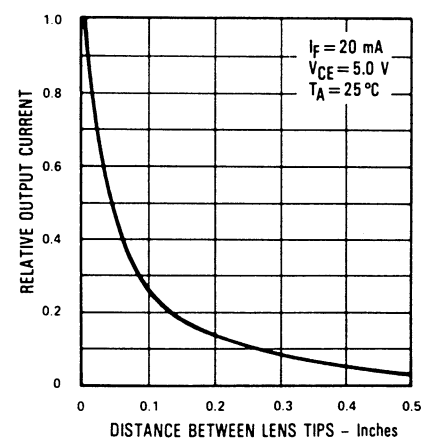
- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. A max. of 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly 1.33 mW/ $^\circ\text{C}$.

Typical Performance Curves

Percent Changes in Radiant Intensity vs Time



Coupling Characteristics of OP266W and OP506W



Type OP266W

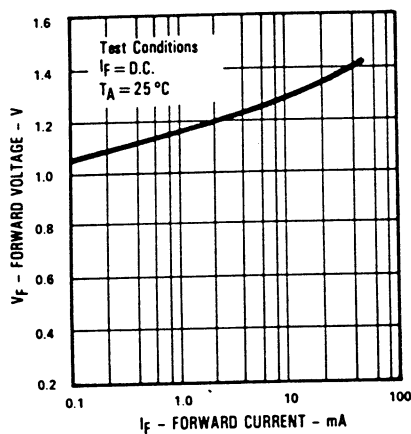
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
P_O	Radiant Power Output	1.00			mW	$I_F = 20\text{ mA}$
V_F	Forward Voltage			1.80	V	$I_F = 20\text{ mA}$
I_R	Reverse Current			100	μA	$V_R = 2\text{ V}$
λ_p	Wavelength at Peak Emission		890		nm	$I_F = 10\text{ mA}$
B	Spectral Bandwidth Between Half Power Points		80		nm	$I_F = 10\text{ mA}$
$\Delta\lambda_p/\Delta T$	Spectral Shift with Temperature		+0.18		$\text{nm}/^\circ\text{C}$	$I_F = \text{Constant}$
θ_{HP}	Emission Angle at Half Power Points		90		Deg.	$I_F = 20\text{ mA}$
t_r	Output Rise Time		500		ns	$I_{F(PK)} = 100\text{ mA}$, PW = $10\ \mu\text{s}$, D.C. = 10%
t_f	Output Fall Time		250		ns	$I_{F(PK)} = 100\text{ mA}$, PW = $10\ \mu\text{s}$, D.C. = 10%

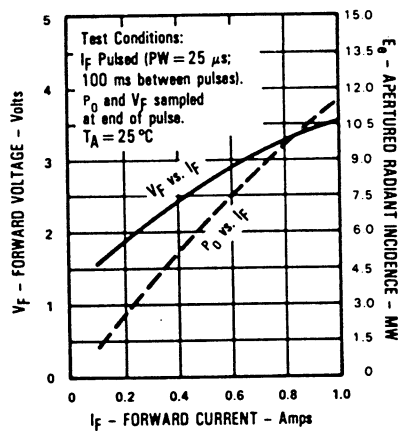
INFRARED
EMITTING
DIODES

Typical Performance Curves

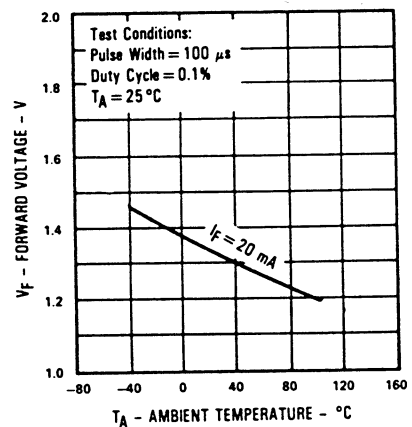
Forward Voltage vs Forward Current



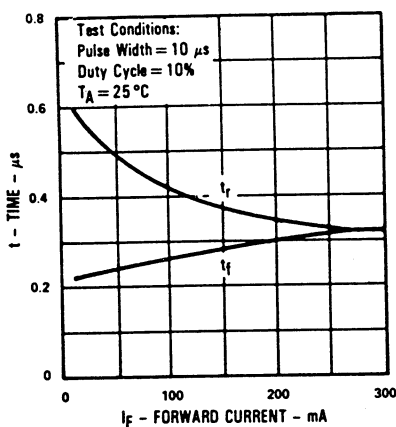
Forward Voltage and Radiant Incidence vs Forward Current



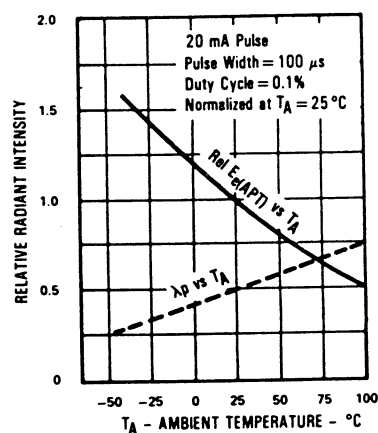
Forward Voltage vs Ambient Temperature



Rise Time and Fall Time vs Forward Current



Relative Radiant Intensity and Wavelength at Peak Emission vs Ambient Temperature



Relative Radiant Intensity vs Angular Displacement

